

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-47. (Canceled)

48. (Currently Amended) A semiconductor device comprising:
a pair of flexible insulating substrates opposing to each other;
a resinous layer formed over one of the pair of the flexible insulating substrates;
a thin film transistor formed over the resinous layer, the thin film transistor having
a semiconductor film comprising silicon; and
a layer comprising resin covering the thin film transistor,
wherein the semiconductor device is flexible.

49.-51. (Canceled)

52. (Currently Amended) A semiconductor device comprising:
a pair of flexible insulating substrates opposing to each other;
a resinous layer formed over one of the pair of the flexible insulating substrates;
a thin film transistor formed over the resinous layer, the thin film transistor having
a semiconductor film comprising crystalline silicon; and
a layer comprising resin covering the thin film transistor,
wherein the semiconductor device is flexible.

53.-55. (Canceled)

56. (Currently Amended) A semiconductor device comprising:

a pair of flexible insulating substrates opposing to each other;
a resinous layer formed over one of the pair of the flexible insulating substrates;
a thin film transistor formed over the resinous layer; and
a layer comprising resin covering the thin film transistor,
wherein the thin film transistor has a semiconductor film comprising a crystalline silicon, and
wherein the crystalline silicon is formed by a laser irradiation,
wherein the semiconductor device is flexible.

57.-60. (Canceled)

61. (Previously Presented) A semiconductor device according to claim 48, wherein the silicon is amorphous silicon.

62. (Previously Presented) A semiconductor device according to claim 48, wherein the silicon is microcrystalline silicon.

63. (Previously Presented) A semiconductor device according to claim 56, wherein the laser irradiation is conducted by using at least one selected from the group consisting of KrF excimer laser and XeCl laser.

64.-65. (Canceled)

66. (Currently Amended) A semiconductor device according to any one of claims 48, 52 and 56, wherein the flexible insulating substrate comprises a plastic substrate.

67. (Currently Amended) A semiconductor device according to any one of claims 48, 52 and 56, wherein the flexible insulating substrate comprises at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

68. (Previously Presented) A semiconductor device according to any one of claims 48, 52 and 56, wherein the resinous layer comprises an acrylic resin.

69. (Previously Presented) A semiconductor device according to any one of claims 48, 52 and 56, wherein the resinous layer comprises at least one selected from the group consisting of methyl esters of acrylic acid, ethyl esters of acrylic acid, butyl esters of acrylic acid, and 2-ethylhexyl esters of acrylic acid.

70. (Previously Presented) A semiconductor device according to any one of claims 48, 52 and 56, wherein the thin film transistor comprises an inverted-staggered thin-film transistor.

71. (Previously Presented) A semiconductor device according to any one of claims 48, 52 and 56, wherein the thin film transistor comprises a coplanar thin-film transistor.

72.-84. (Canceled)